

APT8075AN 800V 11.5A 0.75 Ω
APT7575AN 750V 11.5A 0.75 Ω
APT8090AN 800V 10.5A 0.90 Ω
APT7590AN 750V 10.5A 0.90 Ω

POWER MOS IV™

N - CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT				UNIT
		7575AN	8075AN	7590AN	8090AN	
V _{DSS}	Drain-Source Voltage	750	800	750	800	Volts
I _D	Continuous Drain Current	11.5		10.5		Amps
I _{DM}	Pulsed Drain Current ¹	46		42		Amps
V _{GS}	Gate-Source Voltage	±30				Volts
P _D	Total Power Dissipation @ T _C = 25°C, Derate Above 25°C	230				Watts
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 to 150				°C

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu\text{A}$)	APT8075AN / APT8090AN	800			Volts
		APT7575AN / APT7590AN	750			Volts
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)				250	μA
	($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)				1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)				± 100	nA
$I_{D(ON)}$	On State Drain Current ² ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT8075AN / APT7575AN	11.5			Amps
		APT8090AN / APT7590AN	10.5			Amps
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1\text{mA}$)		2		4	Volts
$R_{DS(ON)}$	Static Drain-Source On-State Resistance ² ($V_{GS} = 10V, I_D = 0.5 I_D [\text{Cont.}]$)	APT8075AN / APT7575AN			0.75	Ohms
		APT8090AN / APT7590AN			0.90	Ohms

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.53	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			30	$^\circ\text{C/W}$
T_L	Max. Lead Temp. for Soldering Conditions: 0.063" from Case for 10 Sec.			300	$^\circ\text{C}$

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Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		2410	2950	pF
C_{oss}	Output Capacitance			370	520	pF
C_{rss}	Reverse Transfer Capacitance			120	180	pF
Q_g	Total Gate Charge ³	$V_{GS} = 10V, I_D = I_D [\text{Cont.}]$ $V_{DD} = 0.5 V_{DSS}$		88	130	nC
Q_{gs}	Gate-Source Charge			8.9	13	nC
Q_{gd}	Gate-Drain ("Miller") Charge			44	67	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}], V_{GS} = 15V$ $R_G = 1.8$		13	27	ns
t_r	Rise Time			18	36	ns
$t_{d(off)}$	Turn-off Delay Time			62	94	ns
t_f	Fall Time			24	48	ns

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

T-39-15

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT8075AN / APT7575AN		11.5	Amps
		APT8090AN / APT7590AN		10.5	Amps
I_{SM}	Pulsed Source Current ¹ (Body Diode)	APT8075AN / APT7575AN		46	Amps
		APT8090AN / APT7590AN		42	Amps
V_{SD}	Diode Forward Voltage ² ($V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}], dI_S/dt = 100A/\mu s$)	328	656	1300	ns
Q_{rr}	Reverse Recovery Charge	3.1	6.2	12	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1\text{ Sec.}$	230			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}], V_{DS} = P_D / I_D [\text{Cont.}], t = 1\text{ Sec.}$	230			Watts
I_{LM}	Inductive Current Clamped	APT8075AN / APT7575AN	46			Amps
		APT8090AN / APT7590AN	42			Amps

- 1.) Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)
- 2.) Pulse Test: Pulse width < 380 μs
Duty Cycle < 2%
- 3.) See MIL-STD-750 Method 3471

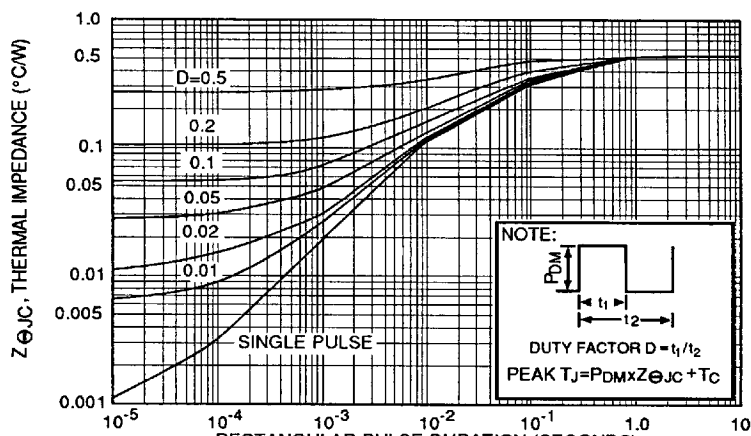


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

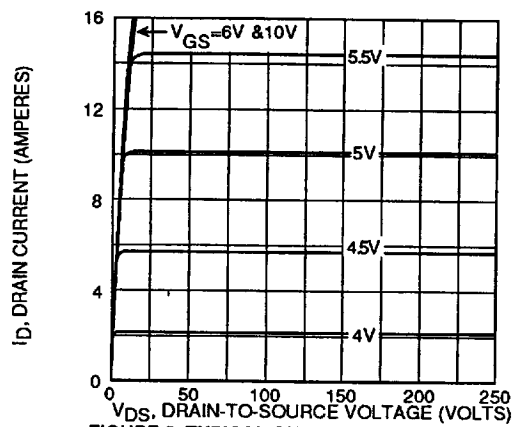


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

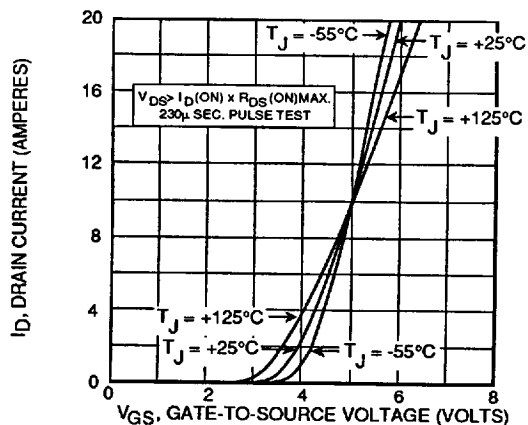


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

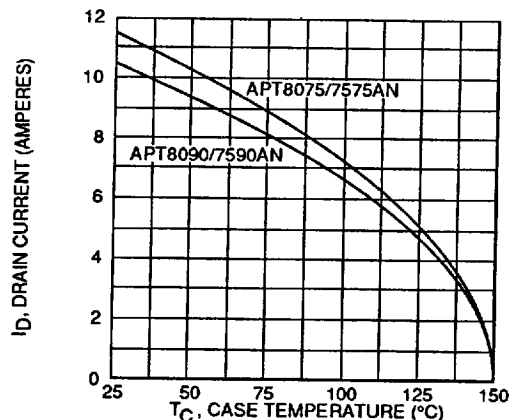


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

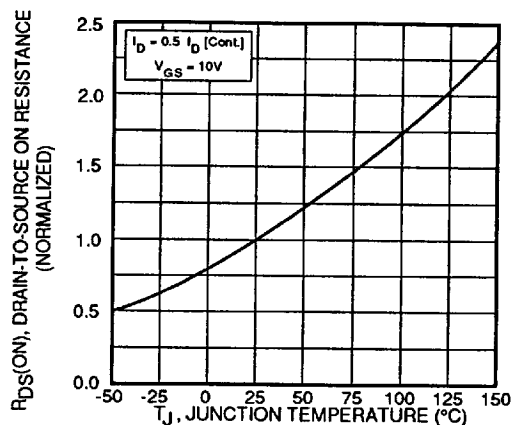


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

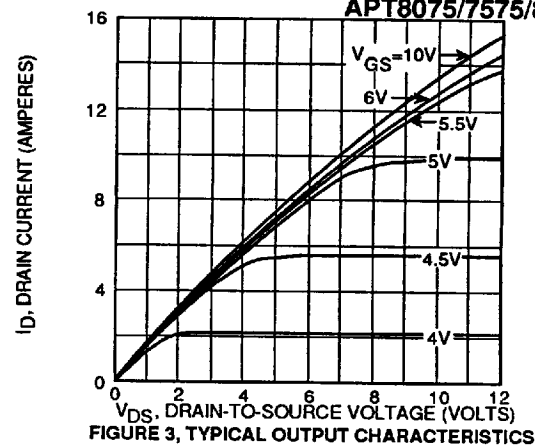


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

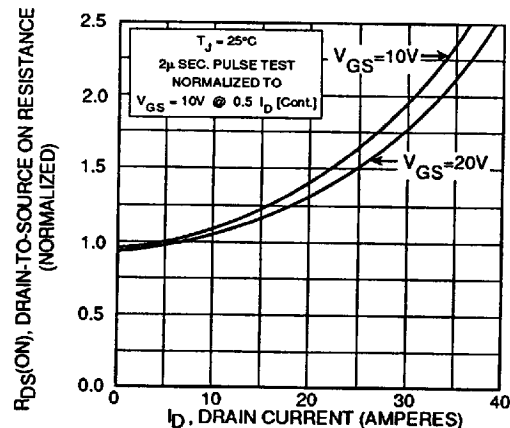
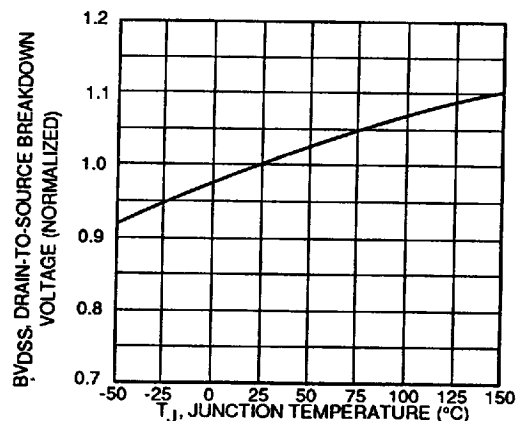
FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

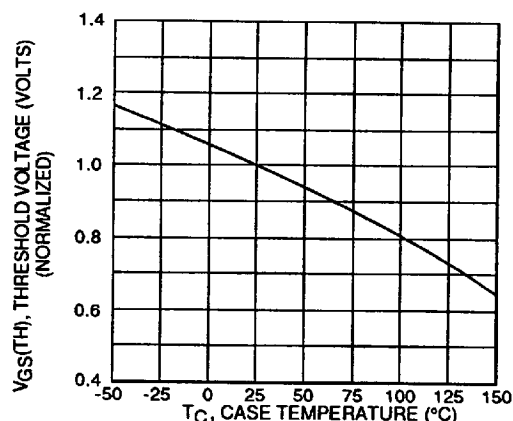


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

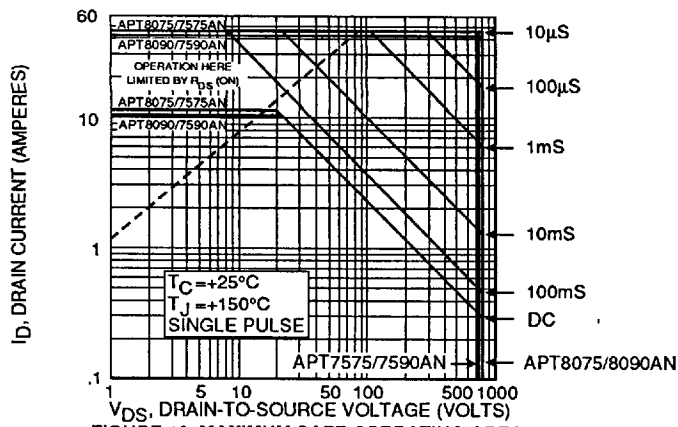


FIGURE 10, MAXIMUM SAFE OPERATING AREA

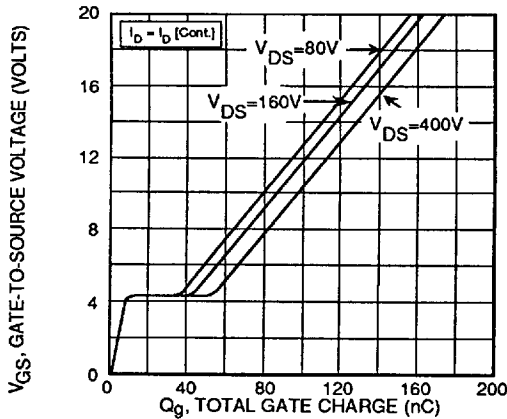


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

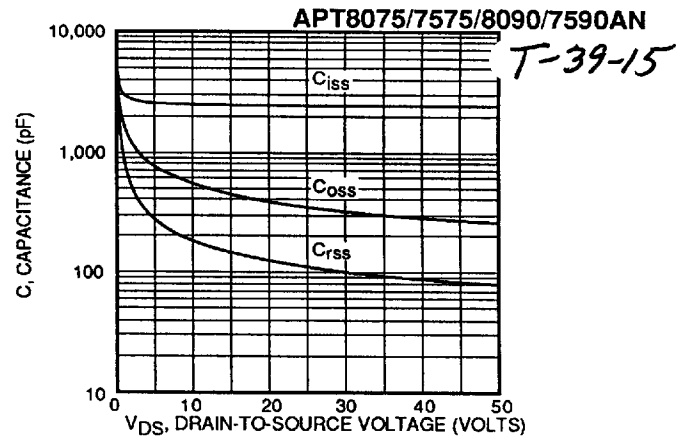


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

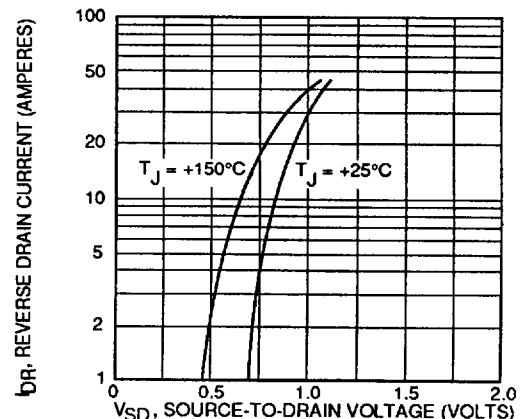
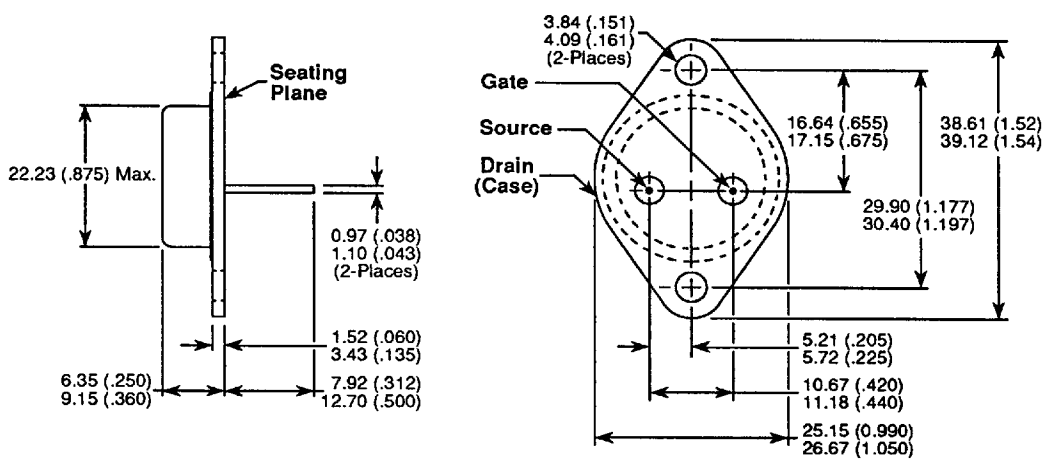


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-3 Package Outline (TO-204AA)



Dimensions in Millimeters and (Inches)